



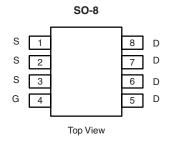
# **N-Channel 30-V MOSFET**

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)		
30	0.0045 at V <sub>GS</sub> = 10 V	20	24		
	$0.006$ at $V_{GS} = 4.5 \text{ V}$	17	24		

#### **FEATURES**

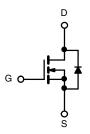
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFETs
- 100 % R<sub>g</sub> Tested





Ordering Information: Si4430BDY-T1-E3 (Lead (Pb)-free)

Si4430BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b>	$T_A = 25$ °C, unles	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	30		V
Gate-Source Voltage		V <sub>GS</sub>	± 20		
Continuous Dunin Courset /T 150 °C\d	T <sub>A</sub> = 25 °C	I-	20	14	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C	- I <sub>D</sub>	16	11	
Pulsed Drain Current		I <sub>DM</sub>	± 60		Α
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	2.7	1.40	
Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	40		
Single Pulse Avalanche Energy	L = 0.1 IIII	E <sub>AS</sub>	80		mJ
	T <sub>A</sub> = 25 °C	3.0 1.6		1.6	W
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	- P <sub>D</sub>	2.0	1.0	VV
Operating Junction and Storage Temperature Ran	T <sub>J</sub> , T <sub>stg</sub>	- 55	i to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Typical	Maximum	Unit		
M :	t ≤ 10 s	$R_{thJA}$	34	41		
Maximum Junction-to-Ambient (MOSFET) <sup>a</sup>	Steady State		67	80	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	15	19		

#### Notes

a. Surface Mounted on 1" x 1" FR4 board.

# Vishay Siliconix



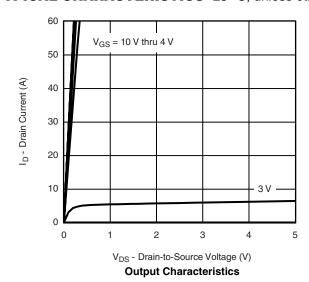
MOSFET SPECIFICATIONS T <sub>J</sub> = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions N		Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$ 1.0			3.0	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zara Cata Valtaga Drain Current	1	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$			10	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			Α	
	В	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		0.0037	0.0045	0	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 17 \text{ A}$		0.0048	0.006	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		80		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 2.7 \text{ A}, V_{GS} = 0 \text{ V}$		0.72	1.1	V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_g$			24	36		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$		10.5		nC	
Gate-Drain Charge	$Q_{gd}$			7.5			
Gate Resistance	$R_g$		0.5	1.1	1.7	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			20	30		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 15 V, $R_L$ = 15 $\Omega$		14	22		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ 1 A, $V_{GEN}$ = 10 V, $R_g$ = 6 $\Omega$		60	90	ns	
Fall Time	t <sub>f</sub>			18	30		
Course Drain Boyeres Bossyery Time	t <sub>rr</sub>	I <sub>E</sub> = 2.7 A, dl/dt = 100 A/μs		35	50		
Source-Drain Reverse Recovery Time	Q <sub>rr</sub>	1F - 2.7 A, αι/αι = 100 A/μs		32	50	nC	

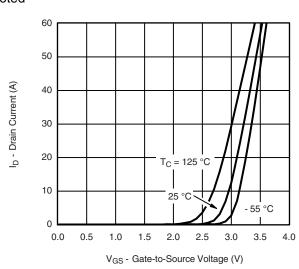
#### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

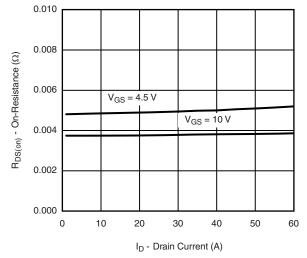




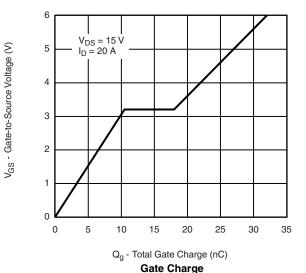
**Transfer Characteristics** 



# TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

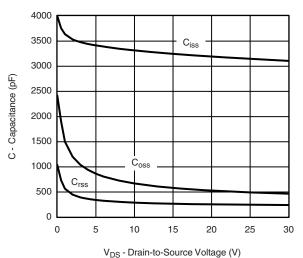


#### On-Resistance vs. Drain Current



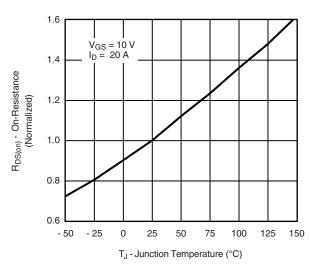
 $T_{J} = 150 \, ^{\circ}\text{C}$   $T_{J} = 150 \, ^{\circ}\text{C}$   $T_{J} = 25 \, ^{\circ}\text{C}$   $0.00 \quad 0.2 \quad 0.4 \quad 0.6 \quad 0.8 \quad 1.0 \quad 1.2$   $V_{SD} - \text{Source-to-Drain Voltage (V)}$ 

Source-Drain Diode Forward Voltage

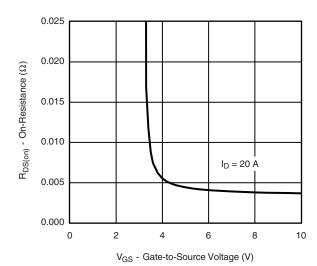


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## Capacitance



#### On-Resistance vs. Junction Temperature



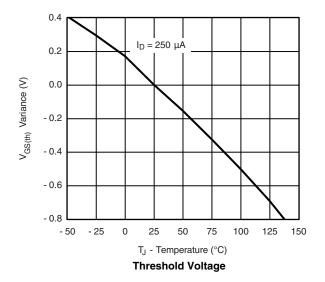
On-Resistance vs. Gate-to-Source Voltage

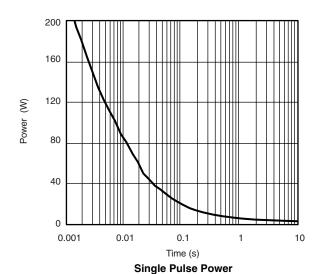
Is - Source Current (A)

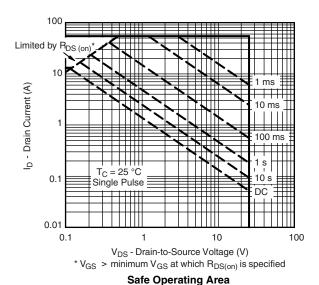
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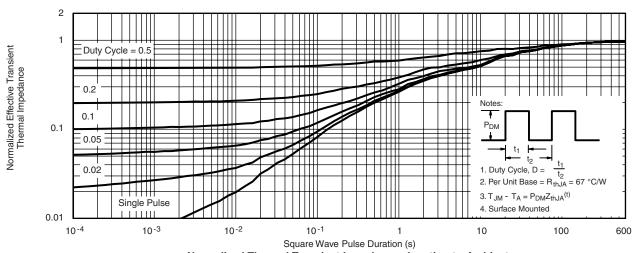
# VISHAY.

## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





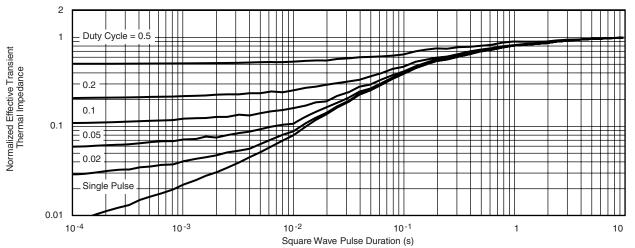




Normalized Thermal Transient Impedance, Junction-to-Ambient



## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INCHES			
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A <sub>1</sub>	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27 BSC		0.050	)50 BSC		
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I. 11-Sep-06						

DWG: 5498

Document Number: 71192 www.vishay.com 11-Sep-06



## **RECOMMENDED MINIMUM PADS FOR SO-8**



Recommended Minimum Pads Dimensions in Inches/(mm)

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